

INTEGRATED CIRCUIT WITH PROTECTED IMPLANTATION PROFILES AND METHOD FOR THE FORMATION THEREOF

ABSTRACT

5 A method for manufacturing an integrated circuit structure includes providing a semiconductor substrate and forming at least one oxide-nitride-oxide dielectric layer above the semiconductor substrate. At least one implantation is formed into at least one area of the semiconductor substrate beneath the oxide-nitride-oxide dielectric layer subsequent to the formation of the oxide-nitride-oxide dielectric layer.

10 Figure 5